

REMARKS

The application was filed with claims 1-4, of which claim 3 is a multiple dependent claim which depends from claim 1 or 2. Claim 3 is being amended so as to depend exclusively from claim 1, and new claim 5 is being presented in order to set forth claim 3 in a form which depends exclusively from claim 2, thereby eliminating the multiple dependency of claim 3. Marked up versions of the amended claim is attached hereto pursuant to 37 C.F.R. § 1.121(c)(ii).

Therefore, an action on the application as amended herein is respectfully requested.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at the Los Angeles telephone number (213) 337-6742 to discuss the steps necessary for placing the application in condition for allowance.

If there are any fees due in connection with the filing of this response, please charge the fees to our Deposit Account No. 50-1314.

Respectfully submitted,

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Date: April 18, 2002

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Version with markings to show changes made:

Rewrite claim 3 as follows:

3. (Amended) The method for growing a semiconductor single crystal according to Claim 1 [or 2], wherein electric power values of the heater surrounding the crucible and the subsidiary heating means and/or a ratio of the both power values are obtained by calculation based on global heat transfer analysis, the obtained value(s) is/are used as a target value or values of control, and electric powers supplied to the heater and the subsidiary heating means are controlled to be as near the target value or values as possible during the pulling of the single crystal.

Please add the following new claim:

--5. The method for growing a semiconductor single crystal according to Claim 2, wherein electric power values of the heater surrounding the crucible and the subsidiary heating means and/or a ratio of the both power values are obtained by calculation based on global heat transfer analysis, the obtained value(s) is/are used as a target value or values of control, and electric powers supplied to the heater and the subsidiary heating means are controlled to be as near the target value or values as possible during the pulling of the single crystal. --